TECHNICAL DATA DATA SHEET 786, REV. B

# SILICON SCHOTTKY RECTIFIER Very Low Forward Voltage Drop

## Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

# **Maximum Ratings**

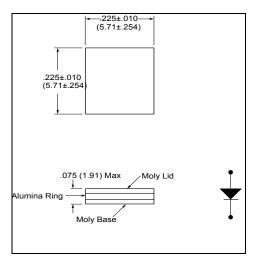
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	60	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle, rectangular	30	Α
Current		wave form		
Max. Peak One Cycle Non-	I <sub>FSM</sub>	8.3 ms, half Sine wave	1020	Α
Repetitive Surge Current				
Non-Repetitive Avalanche	$E_AS$	$T_J = 25 ^{\circ}\text{C}, I_{AS} = 11.5 \text{A},$	13	mJ
Energy		L = 11.5 mH		
Repetitive Avalanche Current	$I_{AR}$	I <sub>AS</sub> decay linearly to 0 in 1 μs	1.5	Α
		f limited by T <sub>J</sub> max V <sub>A</sub> =1.5V <sub>R</sub>		
Maximum Thermal Resistance	$R_{\scriptscriptstyle{ hetaJC}}$		1.7	°C/W
Maximum Thermal Redictation			1.7	0, 11
Max. Junction Temperature	$T_J$	-	-55 to +150	°C
Max. Storage Temperature	$T_{stg}$	-	-55 to +150	°C

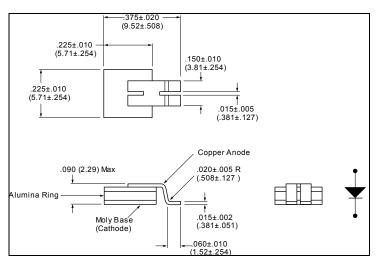
# **Electrical Characteristics**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 15A, Pulse, T <sub>J</sub> = 25 °C	0.60	V
	$V_{F2}$	@ 15A, Pulse, T <sub>J</sub> = 125 °C	0.56	V
Max. Reverse Current	I <sub>R1</sub>	@V <sub>R</sub> = 60V, Pulse,	0.8	mA
		T <sub>J</sub> = 25 °C		
	I <sub>R2</sub>	@V <sub>R</sub> = 60V, Pulse,	45	mA
		T <sub>J</sub> = 125 °C		
Max. Junction Capacitance	C <sub>T</sub>	$@V_R = 5V, T_C = 25  ^{\circ}C$	720	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

## DATA SHEET 786, REV. B

#### **MECHANICAL DIMENSIONS: In Inches / mm**



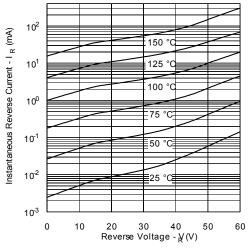


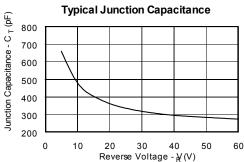
SHD-1B

#### **Typical Forward Characteristics**

# 

#### **Typical Reverse Characteristics**





SE	N	9	IT	P	<b>^</b>	N	ı
o e	ıv			м	.,	и	

**DATA SHEET 786, REV. B** 

#### DISCLAIMER:

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.